

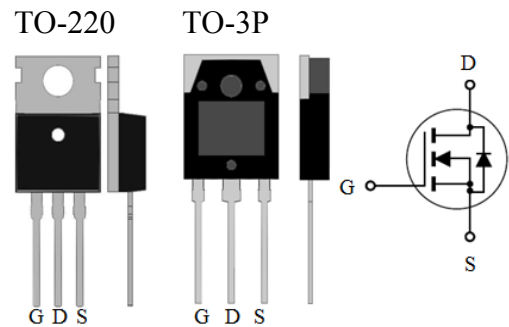
60V N-Channel MOSFET
Applications:

- High Speed Power Switching
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

V_{DS}	$R_{DS(ON)}(MAX)$	I_D
60V	5.7m Ω	142A

Features:

- Lead Free
- Low $R_{DS(ON)}$ to Minimize Conductive Loss
- Low Gate Charge for Fast Switching Application
- Optimized $V_{(BR)DSS}$ Ruggedness



Pin Definition and Inner Circuit

Ordering Information

Park Number	Package	Brand
MXP65D7AT	TO220	MXP
MXP65D7AQ	TO-3P	

Absolute Maximum Ratings
 $T_c=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current	Silicon Limited	142
		Package Limited	80
I_{DM}	Pulsed Drain Current @ $V_{GS}=10V$	569	A
P_D	Power Dissipation	231	W
V_{GS}	Gate-to-Source Voltage	+/-20	V
T_J and T_{stg}	Operating Junction and Storage Temperature Range	-55 to 175	$^{\circ}C$

Avalanche Characteristics
 $T_c=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Unit
E_{AS} ①	Single Pulse Avalanche Energy ($V_{DS}=30V$, $V_{GS}=10V$, $R_g=25\Omega$, $L=1mH$)	200	mJ
I_{AS}	Single Pulse Avalanche Current	Figure 9	A

Thermal Resistance

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.65	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	$^{\circ}C/W$

① : Guarantee number.

60V N-Channel MOSFET
OFF Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	-	-	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	-	-	1	μA	$V_{DS}=48V, V_{GS}=0V$
		-	-	100		$V_{DS}=48V, V_{GS}=0V, T_J=125^{\circ}\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	-	-	100	nA	$V_{GS}=+20V$
	Gate-to-Source Reverse Leakage	-	-	100		$V_{GS}=-20V$

ON Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

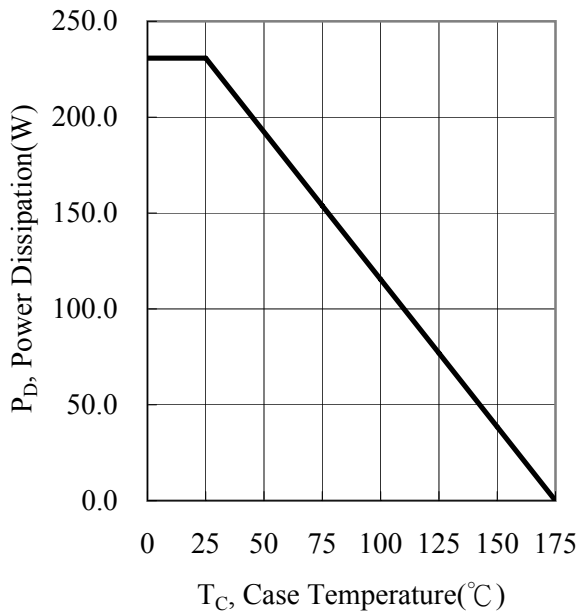
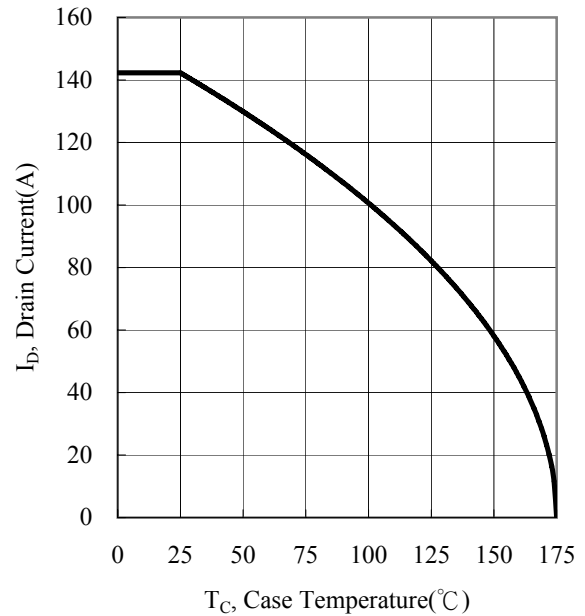
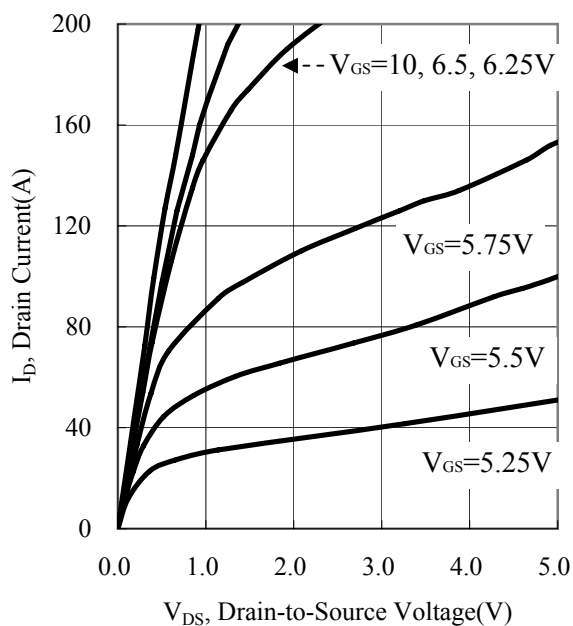
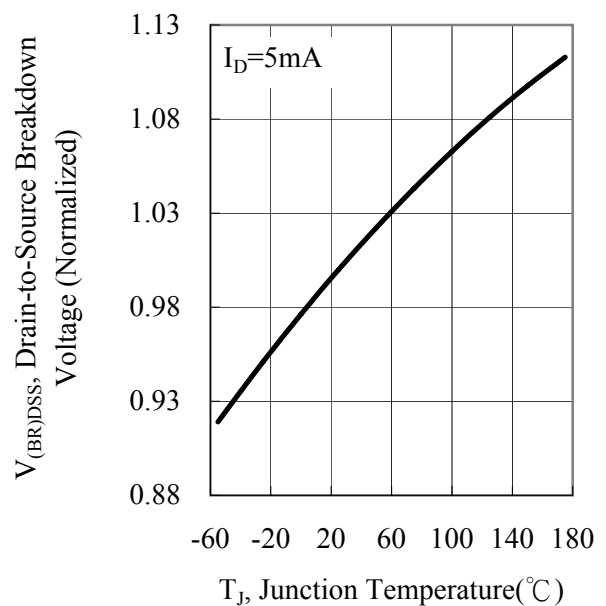
Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	-	4.2	5.7	$m\Omega$	$V_{GS}=10V, I_D=80A$
$V_{GS(th)}$	Gate Threshold Voltage	2	-	4	V	$V_{GS}=V_{DS}, I_D=250\mu A$

Dynamic Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
C_{iss}	Input Capacitance	-	4696.0	-	pF	$V_{GS}=0V, V_{DS}=30V,$ $f=1.0MHz$
C_{oss}	Output Capacitance	-	610.2	-		
C_{rss}	Reverse Transfer Capacitance	-	242.7	-		
Q_g	Total Gate Charge	-	62.8	-	nC	$V_{DD}=30V, I_D=80A, V_{GS}=10V$
Q_{gs}	Gate-to-Source Charge	-	19.8	-		
Q_{gd}	Gate-to-Drain ("Miller") Charge	-	13.5	-		
$T_d(on)$	Turn-on Delay Time	-	22.4	-	ns	$V_{DD}=30V, I_D=40A,$ $V_{GS}=10V, R_G=10\Omega,$ $R_L=0.75\Omega$
T_r	Rise Time	-	50.3	-		
$T_d(off)$	Turn-off Delay Time	-	60.8	-		
T_f	Fall Time	-	36.4	-		

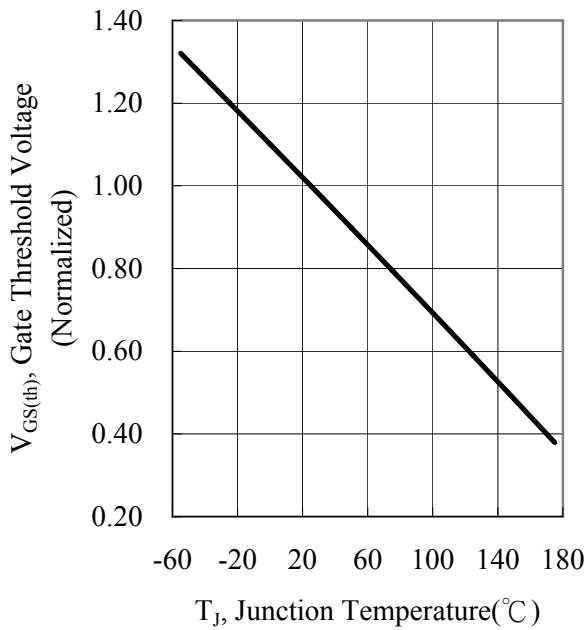
Source-Drain Diode Characteristics
 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
V_{SD}	Diode Forward Voltage	-	-	1.2	V	$I_S=80A, V_{GS}=0V$
T_{rr}	Reverse Recovery Time	-	90.3	-	ns	$I_S=80A, di/dt=100A/\mu s$
Q_{rr}	Reverse Recovery Charge	-	207.3	-	nC	

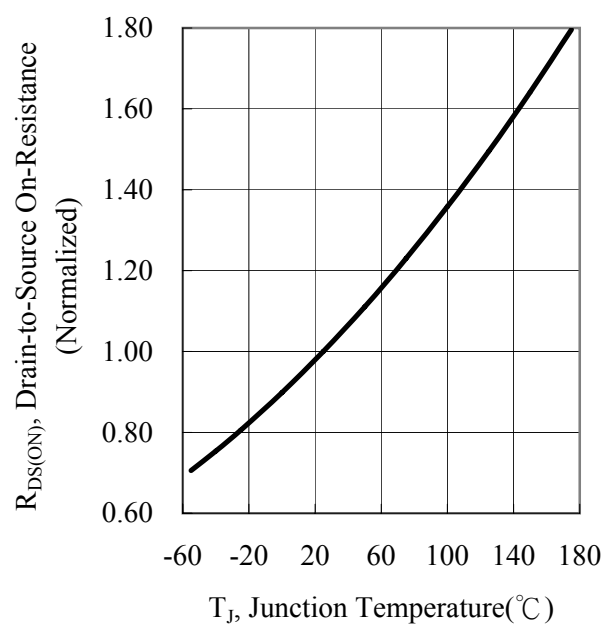
60V N-Channel MOSFET
1. Power Dissipation

2. Drain Current

3. Output Characteristics $T_C=25^\circ\text{C}$

4. Drain-to-Source Breakdown Voltage


60V N-Channel MOSFET

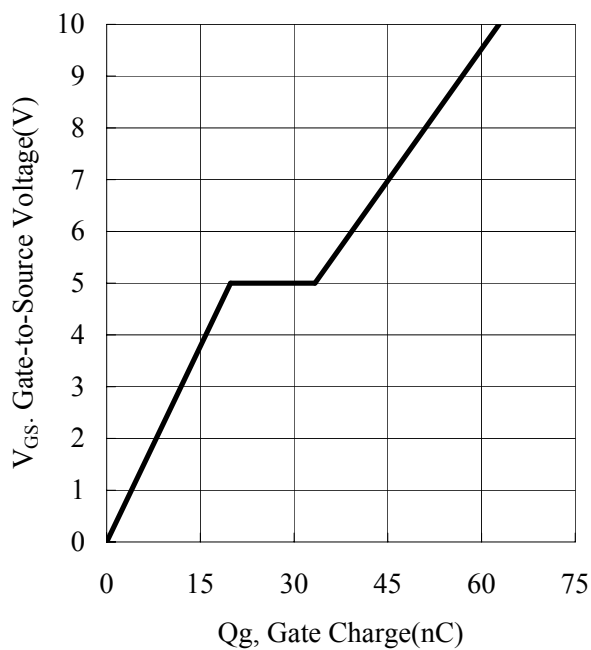
5. Gate Threshold Voltage



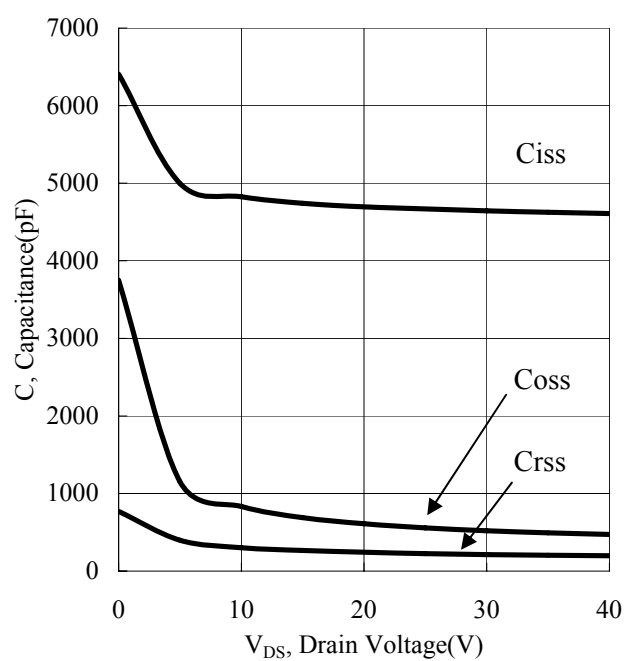
6. Drain-to-Source On-Resistance



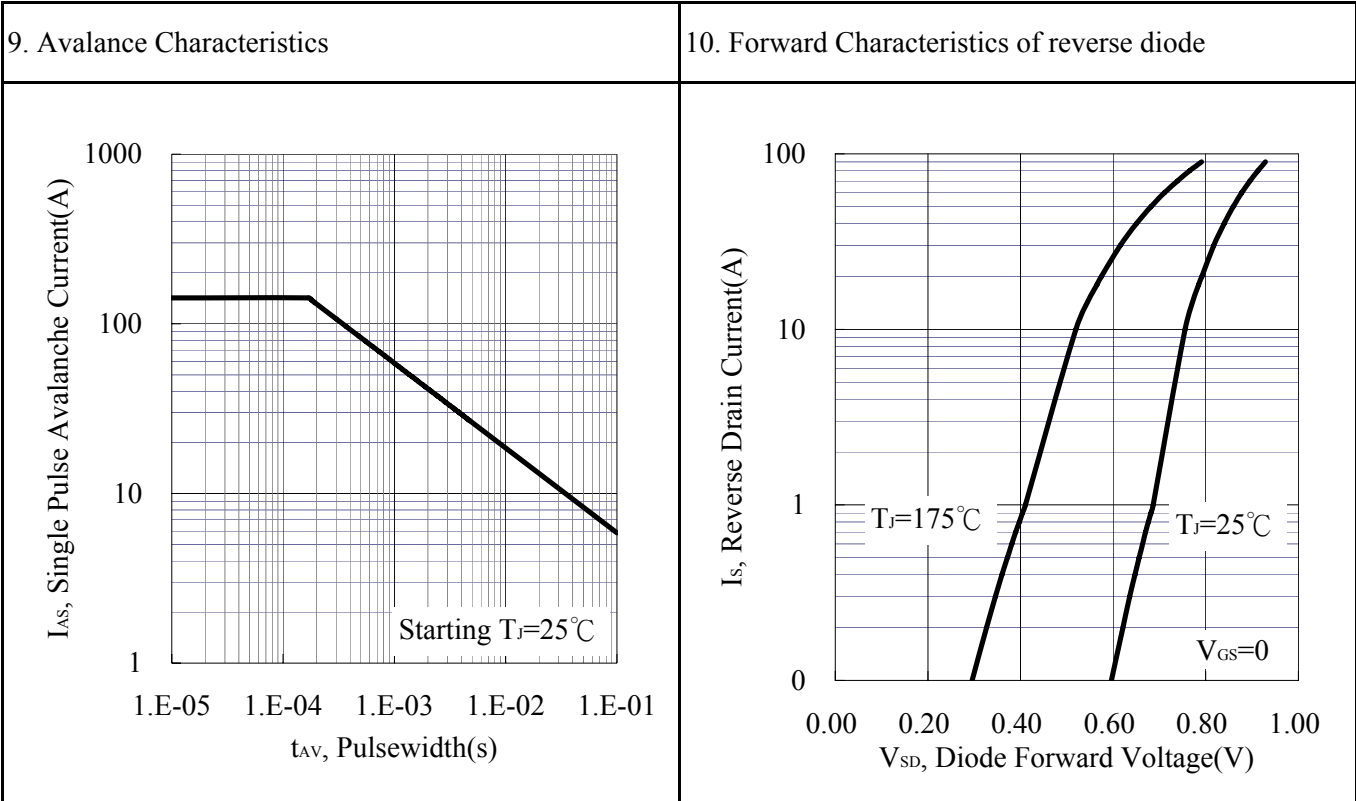
7. Typ. Gate Charge



8. Typ. Capacitance

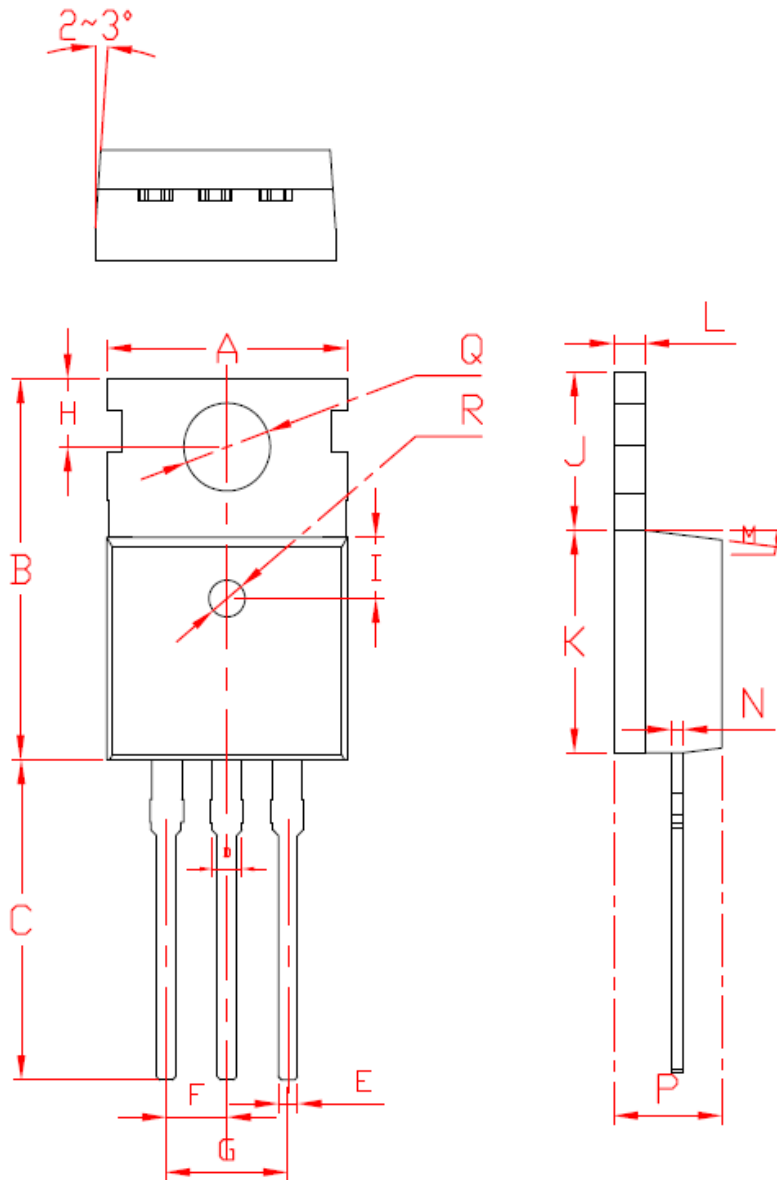


60V N-Channel MOSFET



TO220

1. Outline Dimension

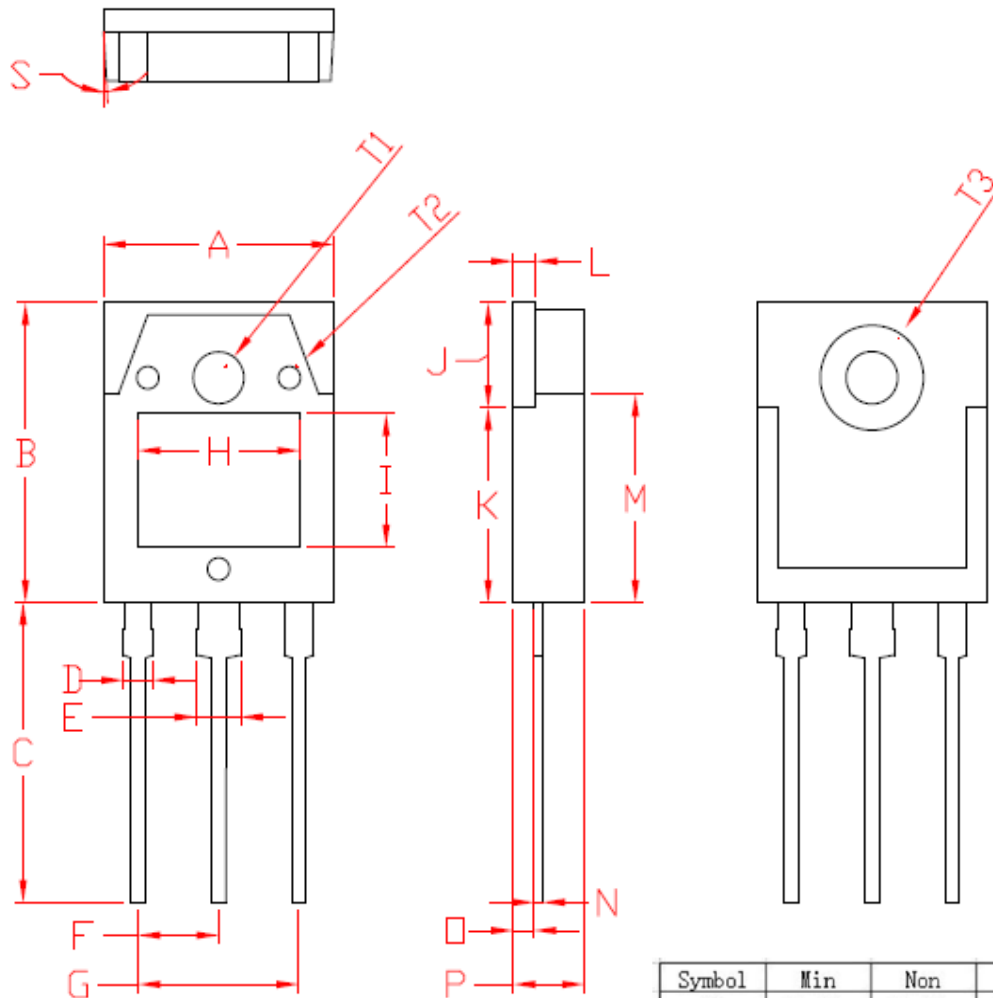


Symbol	A	B	C	D	E	F	G	H	I	J	K	L	M	N	O	P	Q	R
Min	9.8	15.4	12.75					2.73		6.4	9	1.29		0.48	2.35	4.4	3.5	1.4
Non	10	15.6	13.1	1.31	0.8	2.54	5.08	2.8	2.5	6.5	9.1	1.3	1.27	0.5	2.4	4.5	3.6	1.5
Max	10.2	15.8	13.17					2.87		6.6	9.2	1.32		0.56	2.5	4.7	3.63	1.6

UNIT : mm

TO-3P

1. Outline Dimension



Symbol	Min	Non	Max
A	15.50	15.60	15.70
B	19.70	19.90	20.10
C	20.10	20.30	20.50
D		2.00	
E		3.00	
F		5.45	
G		10.90	
H	10.80	10.90	11.00
I	8.80	8.90	9.00
J	6.85	7.00	7.15
K	12.75	12.90	13.05
L	1.49	1.50	1.51
M	13.70	13.85	14.00
N	0.59	0.60	0.61
O	1.32	1.40	1.48
P	4.70	4.80	4.90
S		4°	
T1		3.50	
T2		1.50	
T3		7.00	

UNIT : mm

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